

## Claims

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1. A thin film semiconductor device, comprising:  
 a substrate;  
 an underlevel protection layer comprising an insulating material the underlevel protection layer being formed on at least a portion of the substrate; and  
 a semiconductor film formed on the underlevel protection layer creating an underlevel protection film, the semiconductor film being an active layer of a transistor and having a thickness between about 9 nm and 135 nm, the underlevel protection film comprising a plurality of different films, and the implantation dose is  $1 \times 10^{18} \text{ cm}^{-3}$  or less, a top layer of film and a second layer of film, and the top layer of the underlevel protection film being a silicon oxide film formed on the second layer of film.

2. A thin film semiconductor device, comprising:  
 a glass substrate of 300 mm x 300 mm or more;  
 an underlevel protection layer comprising an insulating material, the underlevel protection layer being formed on at least a portion of the substrate; and  
 a field effect transistor having:  
 three silicon oxide semiconductor films formed as said underlevel protection layer,  
 a gate insulator layer formed on the semiconductor film,  
 a gate electrode formed on the gate insulator layer; and  
 an electrically insulating interlevel insulator layer formed over the gate electrode and between interconnects of said field effect transistor, the thin film semiconductor device having a thickness that is a sum of thicknesses of the underlevel protection layer, the gate insulator layer, and the interlevel insulator layer, and the thickness of the thin film semiconductor device being about  $2 \mu\text{m}$  or less.